

AMENDMENTS TO THE SPECIFICATION

(1) Please replace the paragraph beginning “According to a second” on page 4 of the specification with the following amended paragraph:

According to a second aspect of the present invention, the moisture-permeable film may be formed of ~~silicon~~silicone gel. In general, the dielectric constant of the humidity sensing film is equal to 2 to 6. The ~~silicon~~silicone-based gel has a higher dielectric constant and excellent moisture-permeability. Therefore, when the moisture-permeable film is formed of ~~silicon~~silicone gel, reduction of the response characteristic of the capacitance type humidity sensor can be suppressed by forming the moisture-permeable film.

(2) Please replace the paragraph beginning “The pair of electrodes” on page 7 of the specification with the following amended paragraph:

The pair of electrodes 31, 32 are formed by adhesively attaching metal material such as aluminum, copper, gold, platinum or the like onto the silicon oxide film 20 disposed on the semiconductor substrate 10 by deposition, sputtering or the like, and then subjecting the metal material to patterning in a comb-tooth-shaped pattern.

(3) Please replace the paragraph beginning “The moisture-permeable film” on page 14 of the specification with the following amended paragraph:

The moisture-permeable film 60 is formed of material having excellent moisture-permeability such as ~~silicon~~silicone gel, fluorine gel or the like by a method using droplet or the like. When the moisture permeability of the moisture-permeable film 60 is insufficient, the response characteristic of the capacitance type humidity sensor is lowered.